

Title (en)
METHOD OF POLISHING SEMICONDUCTOR WAFER

Publication
EP 0403287 A3 19911023 (EN)

Application
EP 90306519 A 19900614

Priority
JP 15374889 A 19890616

Abstract (en)
[origin: EP0403287A2] A semiconductor wafer (12) is ground or polished to a desired thickness by pressing the wafer against a rotating turntable (13), characterised in that the semiconductor wafer is bonded to a plate (11), and a thickness-regulating member (15) whose surface is more resistant to polishing/grinding than the semiconductor wafer is arranged on the plate. By way of example, the thickness-regulating member comprises a silicon matrix and has a silicon oxide film at the surface.

IPC 1-7
H01L 21/00

IPC 8 full level
B24B 37/07 (2012.01); **H01L 21/304** (2006.01)

CPC (source: EP)
B24B 37/013 (2013.01)

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Designated contracting state (EPC)
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